

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L58AE

VHF~UHF Band Low Noise Amplifier Applications

- Two devices are built in to the super-thin and extreme super mini (6 pins) package: ES6

Mounted Devices

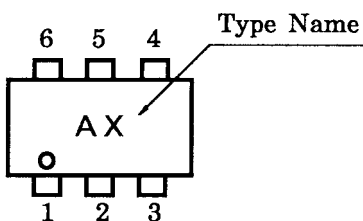
	Q1: SSM (TESM)	Q2: SSM (TESM)
Three-pins (SSM/TESM) mold products are corresponded.	MT3S06S (MT3S06T)	MT3S03AS (MT3S03AT)

Maximum Ratings (Ta = 25°C)

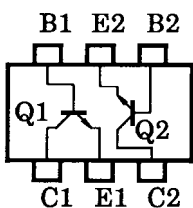
Characteristics	Symbol	Q1	Q2	Unit
Collector-base voltage	V _{CBO}	10	10	V
Collector-emitter voltage	V _{CEO}	5	5	V
Emitter-base voltage	V _{EBO}	1.5	2	V
Collector current	I _C	15	40	mA
Base current	I _B	7	10	mA
Collector power dissipation	P _C (Note 1)	100		mW
Junction temperature	T _j	125		°C
Storage temperature range	T _{stg}	-55~125		°C

Note 1: Total power dissipation of Q1 and Q2.

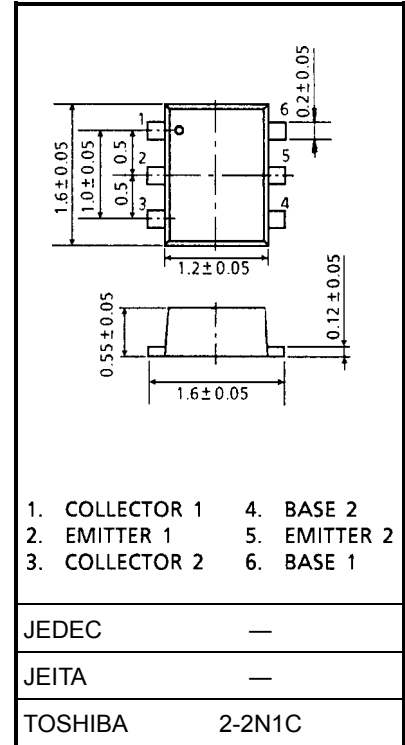
Marking



Pin Assignment (top view)



Unit: mm



Weight: 0.003 g (typ.)

Electrical Characteristics Q1 (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	70	—	140	
Transition frequency	f_T	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}$	7	10	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$	—	7.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 3\text{ V}, I_C = 7\text{ mA}, f = 2\text{ GHz}$	4.5	8	—	
Noise figure	NF (1)	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$	—	1.7	3	dB
	NF (2)	$V_{CE} = 3\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$	—	1.6	3	
Reverse transfer capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note 2)	—	0.35	0.75	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Electrical Characteristics Q2 (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	80	—	160	
Transition frequency	$f_T (1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	5	7	—	GHz
	$f_T (2)$	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}$	7	10	—	
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$	—	5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 3\text{ V}, I_C = 20\text{ mA}, f = 2\text{ GHz}$	3	6.5	—	
Noise figure	NF (1)	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$	—	1.7	3	dB
	NF (2)	$V_{CE} = 3\text{ V}, I_C = 7\text{ mA}, f = 2\text{ GHz}$	—	1.4	2.2	
Reverse transfer capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note 2)	—	0.8	1.15	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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